

**AMENDMENTS TO THE CLAIMS**

1. (Currently amended) A semiconductor light-emitting element mounting member comprising:

a substrate; and

a metal film formed on a surface of said substrate, formed from Ag, Al, or an alloy containing said metals, and functioning as an electrode layer for mounting at least one of a semiconductor light-emitting element and a reflective layer for reflecting light from a semiconductor light-emitting element; wherein:

the thickness of the metal film is 0.5 - 3  $\mu\text{m}$  and;

crystal grains of said metal or alloy forming said metal film have a particle diameter along a surface plane of said metal film is of no more than 0.5  $\mu\text{m}$  and;

said surface of said metal film has a center-line average roughness Ra of no more than 0.1  $\mu\text{m}[[.]]$ ;

an adhesion layer and a barrier layer are formed, in sequence, on said substrate, with said metal film being formed on said barrier layer;

the thickness of the adhesion layer is 0.01-1.00  $\mu\text{m}$ ; and

the thickness of the barrier layer is 0.01-1.50  $\mu\text{m}$ .

2. (Canceled)

3. (Currently amended) A The semiconductor light-emitting element mounting member according to claim 1 wherein said metal film is formed as an alloy of at least one of Ag and Al and other metal, a proportional content of said other metal being 0.001 - 10 percent by weight.

4. (Currently amended) A The semiconductor light-emitting element mounting member according to claim 3 wherein said other metal is at least one type of metal selected from a group consisting of Cu, Mg, Si, Mn, Ti, and Cr.

5. (Canceled)

6. (Currently amended) A The semiconductor light-emitting element mounting member according to claim 1 wherein said metal film is formed from Al alone or from an alloy of Al and other metal.

7. (Currently amended) A The semiconductor light-emitting element mounting member according to claim 1 wherein a thermal expansion coefficient of said substrate is  $1 \times 10^{-6}/K - 10 \times 10^{-6}/K$ .

8. (Currently amended) A The semiconductor light-emitting element mounting member according to claim 1 wherein a thermal conductivity of said substrate is at least 80 W/mK.

9. (Currently amended) A The semiconductor light-emitting element mounting member according to claim 1 wherein said semiconductor light-emitting element mounting member is a flat submount.

10. (Currently amended) A semiconductor light-emitting ~~element mounting member of claim 1 further comprising a semiconductor light emitting element mounted thereto. device, comprising:~~ the semiconductor light-emitting element mounting member of claim 1; and a semiconductor light-emitting element mounted in said semiconductor light-emitting element mounting member.

11. (Currently amended) A The semiconductor light-emitting device according to claim 10 wherein the output of said semiconductor light-emitting element is at least 1 W.

12. (Currently amended) A The semiconductor light-emitting device mounting member according to claim 1 wherein said substrate is an insulative ceramic.

13. (Currently amended) A The semiconductor light-emitting device mounting member according to claim 12 wherein the insulative ceramic is selected from a group consisting of AlN, Al<sub>2</sub>O<sub>3</sub>, SiC, Si<sub>3</sub>N<sub>4</sub>, BeO, BN, and insulative Si.